

### **Amendments to the Claims:**

1. (Currently Amended) A resonant circuit structure comprising:
  - a load;
  - a primary component coupled to a node;
  - a secondary component array coupled to the node, in parallel to the primary component; and
  - a reduction system, intercoupled between the load and the node, and adapted to reduce to the reduction system forming a voltage divider with the primary component for reducing operational voltage at the node to a target value.
2. (Original) The structure of claim 1, wherein the resonant circuit structure comprises an inductive load and a capacitance coupled in series.
3. (Original) The structure of claim 1, wherein the load comprises an antenna.
4. The structure of claim 1, wherein the primary component comprises a capacitive element.
5. (Original) The structure of claim 4, wherein the capacitive element is a capacitor.
6. (Original) The structure of claim 4, wherein the secondary component array comprises a capacitive element.

7. (Original) The structure of claim 6, wherein the capacitive element is a capacitor.

8. (Original) The structure of claim 6, wherein the secondary component array comprises a switchable element.

9. (Original) The structure of claim 8, wherein the switchable element is a transistor.

10. (Currently Amended) A circuitry segment, implementing an RLC resonant circuit structure utilizing integrated and discrete devices, the circuitry segment comprising:

a driver circuit, instantiated within a first integrated semiconductor device;

a primary resistive element, having a first terminal coupled the driver circuit, and a second terminal coupled to a first terminal of an inductive load;

a reduction system, having a first terminal coupled to a second terminal of the inductive load, and having a second terminal coupled to a node;

a primary capacitive element, having a first terminal coupled to the node; and

a secondary component array coupled to the node, in parallel to the primary capacitive element;

wherein the reduction system ~~is adapted to reduce to~~ forms voltage divider with the primary capacitive element for reducing reduce to operational voltage at the node to a target value.

11. (Original) The circuitry segment of claim 10, wherein the RLC resonant circuit structure is a low frequency resonant circuit.
12. (Original) The circuitry segment of claim 10, wherein the RLC resonant circuit structure is a radio frequency resonant circuit.
13. (Original) The circuitry segment of claim 10, wherein the primary resistive element is a resistor.
14. (Original) The circuitry segment of claim 13, wherein the resistor is a discrete component.
15. (Original) The circuitry segment of claim 10, wherein the inductive load is an antenna.
16. (Original) The circuitry segment of claim 15, wherein the antenna is for a base transceiver in a wireless communication system.
17. (Original) The circuitry segment of claim 10, wherein the primary capacitive element comprises a capacitor.
18. (Original) The circuitry segment of claim 10, wherein the primary capacitive element comprises a plurality of capacitors.
19. (Original) The circuitry segment of claim 17, wherein the capacitor is a discrete component.

20. (Original) The circuitry segment of claim 17, wherein the capacitor is integrated within a semiconductor device.

21. (Original) The circuitry segment of claim 10, wherein the secondary component array comprises a capacitor.

22. (Original) The circuitry segment of claim 10, wherein the secondary component array comprises a switchable element.

23. (Original) The circuitry segment of claim 22, wherein the switchable element comprises a transistor.

24. (Original) The circuitry segment of claim 21, wherein the capacitor is a discrete component.

25. (Original) The circuitry segment of claim 21, wherein the capacitor is integrated within a semiconductor device.

26. (Original) The circuitry segment of claim 23, wherein the transistor is integrated within a semiconductor device.

27. (Original) The circuitry segment of claim 10, wherein the reduction system comprises a capacitor.

28. (Original) The circuitry segment of claim 10, wherein the reduction system comprises a plurality of capacitors.

29. (Original) The circuitry segment of claim 27, wherein the capacitor is a discrete component.

30. (Original) The circuitry segment of claim 27, wherein the capacitor is integrated within a semiconductor device.

31. (Currently Amended) A method of producing a tunable resonant circuit, having integrated and discrete devices, the method comprising the steps of:

- providing a driver circuit instantiated within a first integrated semiconductor device;

- providing a primary resistor, having a first terminal coupled the driver circuit, and a second terminal coupled to a first terminal of an inductive load;

- providing a primary capacitor, having a first terminal coupled to a node;

- providing a secondary capacitor having a first terminal coupled to the node;

- providing a transistor having a first terminal coupled to a second terminal of the secondary capacitor, and a second terminal coupled to ground; and

- providing a reduction system, having one or more intercoupled capacitors, a first terminal of which is coupled to a second terminal of the inductive load, and a second terminal of which coupled to the node, adapted to reduce to forming a voltage divider with the primary capacitor for reducing operational voltage at the node to a target value.

32. (Original) The method of claim 31, wherein the step of providing a transistor further comprises providing a transistor instantiated within an integrated semiconductor device.

33. (Original) The method of claim 32, wherein the step of providing a transistor further comprises providing a transistor instantiated within the first integrated semiconductor device.

34. (Original) The method of claim 31, wherein the step of providing a secondary capacitor further comprises providing a secondary capacitor instantiated within an integrated semiconductor device.

35. (Original) The method of claim 34, wherein the step of providing a secondary capacitor further comprises providing a secondary capacitor instantiated within the first integrated semiconductor device.